

14. (new): The transfer substrate according to claim 13, wherein the patterning film is an insulating film.

15. (new): The transfer substrate according to claim 14, wherein the insulating film comprises silicon oxide or silicon nitride.

*W.H.K.*

16. (new): The transfer substrate according to claim 1, wherein, within an area of the substrate covered by the patterning film, the seed film is locally present only in areas generally coincident with the metal electrode receiving portions and interconnection film portions interconnecting the metal electrode receiving portions, and is absent from other areas of the substrate covered by the patterning film.